

IN THE SPECIFICATION

Please Amend Paragraph 001 to recite:

[0001] This application is a continuation in part of US Patent App. Ser. No. 10/358,925 filed February 4, 2003 (NT-020 D), which is a divisional application of US Patent App. Ser. No. 09/740,701 filed December 18, 2000 (NT-020), which is now US Patent No. 6,534,116. This application is also a continuation in part of US Patent App. Ser. No. 10/201,604 filed July 22, 2002 (NT-220), US Patent App. Ser. No. 10/201,606 filed July 22, 2002 (NT-254), and US Patent App. Ser. No. 10/379,265 filed March 3, 2003 (NT-288). This application is also a continuation in part of US Patent App. Ser. No. 09/919,788 filed July 31, 2001 (NT-212) and US Patent App. Ser. No. 09/961,193 filed September 20, 2001 (NT-225), both are also continuation in part of above US Patent App. Ser. No. 09/740,701 filed December 18, 2000 (NT-020) and now US Patent No. 6,534,116. All above patents and applications are incorporated herein by reference.

Please Amend Paragraph 47 to recite

[0047] Although, use of two different chemistries designed for filling high aspect ratio and low aspect ratio features using respectively ECD and ECMD processes is preferred, the same process solution may also be used to perform both process steps by keeping it in room temperature at the ECD step but lowering its temperature at the ECMD step. Examples of such electrochemical processes including electrochemical deposition, electrochemical mechanical deposition and electrochemical mechanical polishing can be found in the following patent applications. US Patent App. Ser. No. 10/201,604 ~~entitled Multi-Step Electrodeposition Process~~ filed July 22, 2002, US Patent App. Ser. No. 10/201,606 filed July 22, 2002 ~~entitled Planar Metal Electrodeposition filed~~, and US Patent App. Ser. No. 10/379,265 ~~entitled Defect Free Thin and Planar Film Deposition~~ filed March 3, 2003, all assigned to common assignee of the present invention and all incorporated herein by reference.